OMRON **EE-SY169A**

Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Terminal No	Name	
A	Anode	
K	Cathode	
C	Collector	
F	Emitter	
E	Emitter	

These dimensions are for the sur-
face A. Other lead wire pitch dimen-
sions are for the case surface.

Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.3
$3 < mm \leq 6$	±0.375
$6 < mm \leq 10$	±0.45
$10 < mm \leq 18$	±0.55
$18 < mm \leq 30$	±0.65

Features

- High-quality model with plastic lenses. •
- Highly precise sensing range with a tolerance of ±0.6 mm horizontally and vertically.

Photomicrosensor

(Reflective)

Convergent reflective model with infrared LED.

Absolute Maximum Ratings (Ta = 25°C)

ltem		Symbol	Rated value
Emitter	Forward current	IF	50 mA (see note 1)
	Pulse forward current	I _{FP}	1 A (see note 2)
	Reverse voltage	V _R	3 V
Detector	Collector–Emitter voltage	V _{CEO}	30 V
	Emitter–Collector voltage	V _{ECO}	
	Collector current	I _C	20 mA
	Collector dissipation	P _C	100 mW (see note 1)
Ambient temperature	Operating	Topr	0°C to 70°C
	Storage	Tstg	–20°C to 80°C
Soldering temperature		Tsol	260°C (see note 3)

1. Refer to the temperature rating chart if the ambient Note: temperature exceeds 25°C.

- 2. The pulse width is 10 μs maximum with a frequency of 100 Hz.
- 3. Complete soldering within 10 seconds.

■ Electrical and Optical Characteristics (Ta = 25°C)

Item		Symbol	Value	Condition
Emitter	Forward voltage	V _F	1.5 V max.	I _F = 30 mA
	Reverse current	I _R	10 μA max.	$V_R = 4 V$
	Peak emission wavelength	λ _P	920 nm typ.	I _F = 20 mA
Detector	Light current	ΙL	160 μA min., 2,000 μA max.	$I_F = 20$ mA, $V_{CE} = 5$ V White paper with a reflection ratio of 90%, d = 4 mm (see note)
	Dark current	I _D	2 nA typ., 200 nA max.	$V_{CE} = 5 V, 0 \ell x$
	Leakage current	I _{LEAK}	2 μA max.	$I_F = 20 \text{ mA}, V_{CE} = 5 \text{ V}$ with no reflection
	Collector–Emitter saturated voltage	V _{CE} (sat)		
	Peak spectral sensitivity wavelength	λ _P	850 nm typ.	V _{CE} = 5 V
Rising time		tr	30 μs typ.	$V_{CC} = 5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega, \text{ I}_{L} = 1 \text{ mA}$
Falling time		tf	30 μs typ.	$V_{CC} = 5 V, R_{L} = 1 k\Omega, I_{L} = 1 mA$

Note: The letter "d" indicates the distance between the top surface of the sensor and the sensing object.